

Supporting Information

Covalent Functionalization of Tin Disulfide with Porphyrin for Ultrafast Optical Limiting

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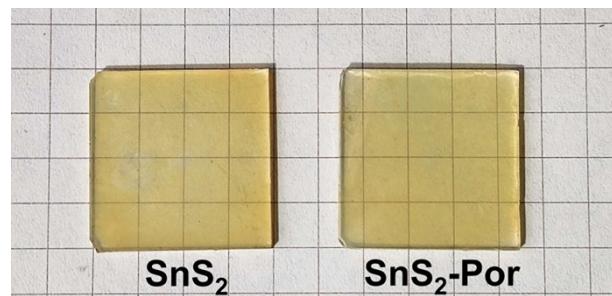


Figure S1. Photographs of the SnS₂ nanosheets and the SnS₂-Por nanohybrid.

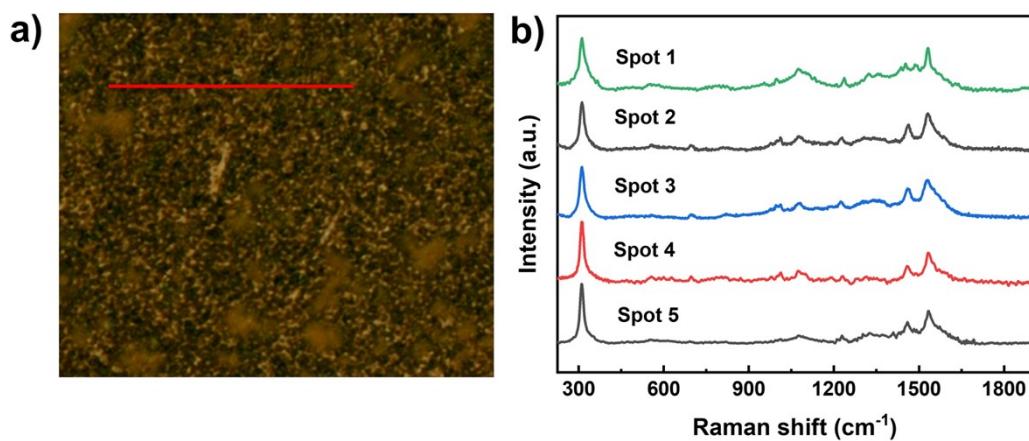


Figure S2. (a) The optical microscopy of the SnS₂-Por nanohybrid. (b) The Raman spectra of 5 spots along the red line in (a).

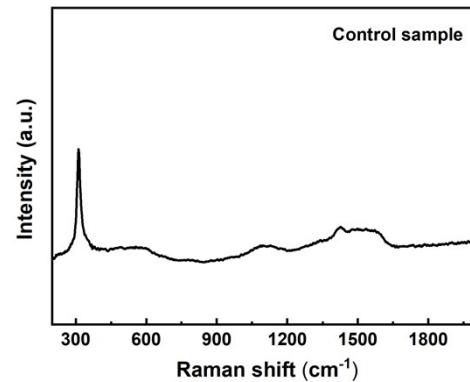


Figure S3. Raman spectrum of the control sample.

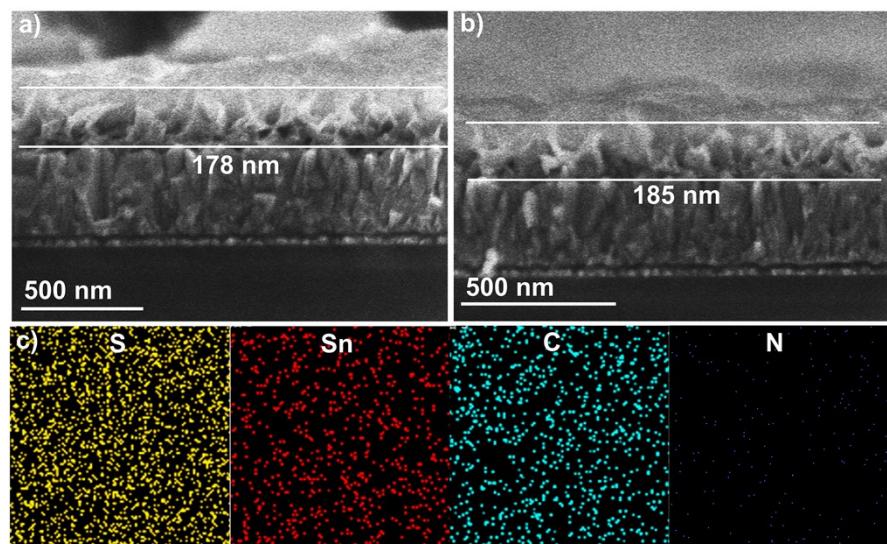


Figure S4. (a) Cross-sectional view SEM image of the SnS₂ nanosheets. (b) Cross-sectional view SEM image of the SnS₂-Por nanohybrid. (c) Elemental mapping images of the SnS₂ nanosheets.

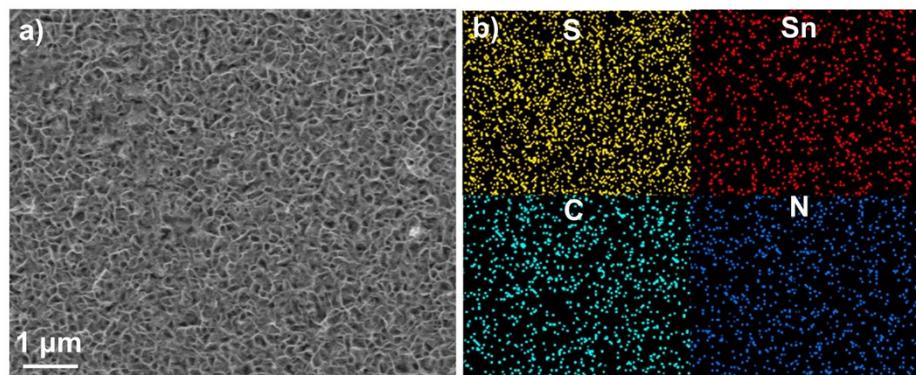


Figure S5. SEM image (a) and the corresponding elemental mapping images (b) of the SnS₂-Por nanohybrid on a larger scale.

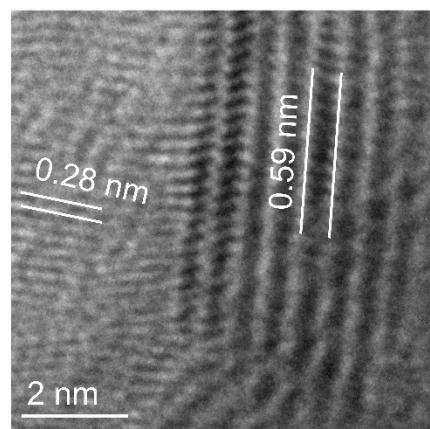


Figure S6. High-resolution TEM image of the SnS₂-Por nanohybrid.

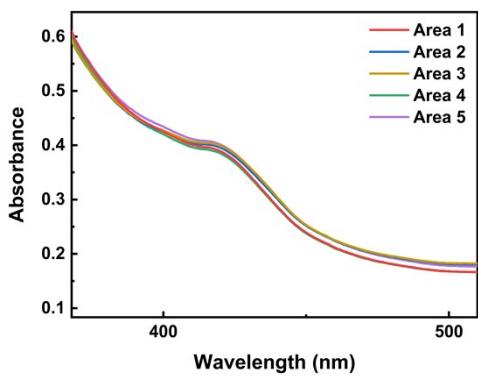


Figure S7. UV-Vis absorption spectra of the SnS_2 -Por nanohybrid at different areas.

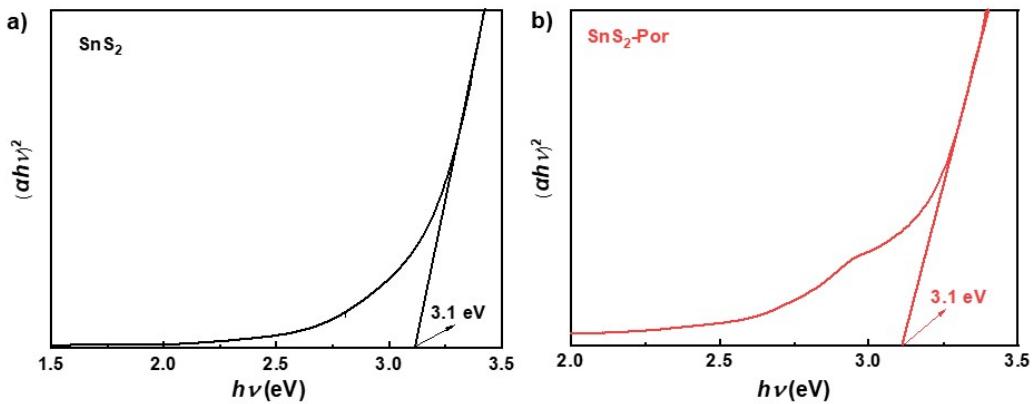


Figure S8. Tauc plots of the SnS_2 nanosheets (a) and the SnS_2 -Por nanohybrid (b).

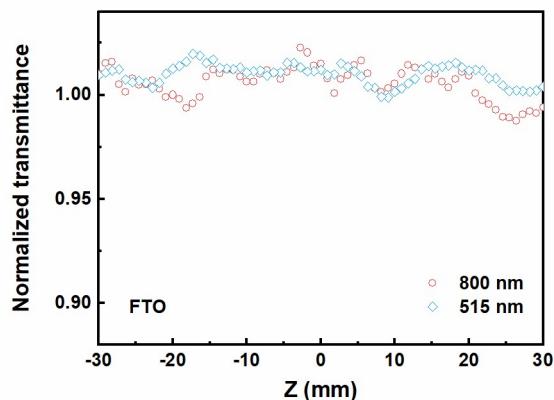


Figure S9. Open-aperture Z-scan curves of the FTO substrate at 800 nm with 56 nJ pulse energy and at 515 nm with 60 nJ pulse energy.

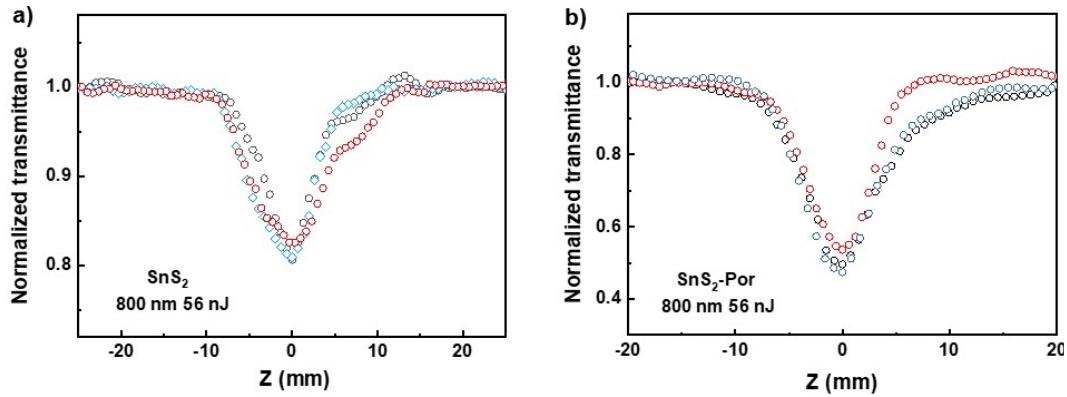


Figure S10. Open-aperture Z-scan curves measured at different points of the SnS₂ nanosheets (a) and the SnS₂-Por nanohybrid (b).

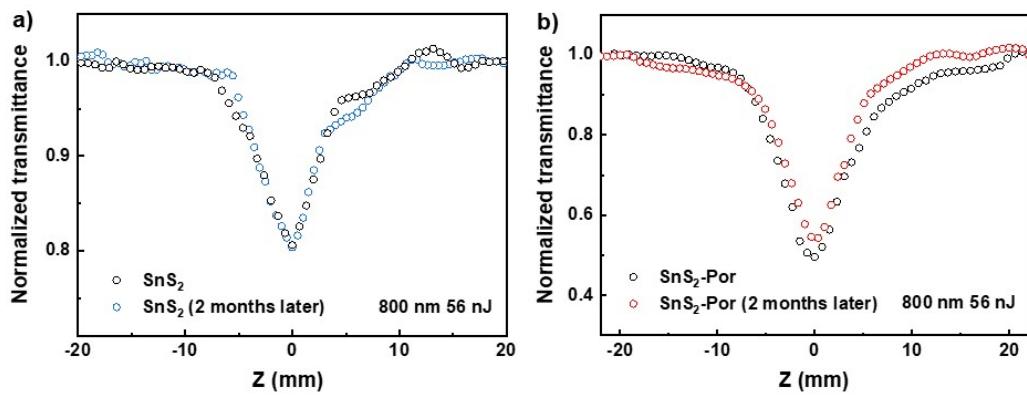


Figure S11. Open-aperture Z-scan curves of the SnS₂ nanosheets (a) and the SnS₂-Por nanohybrid (b) before and after ambient exposure.

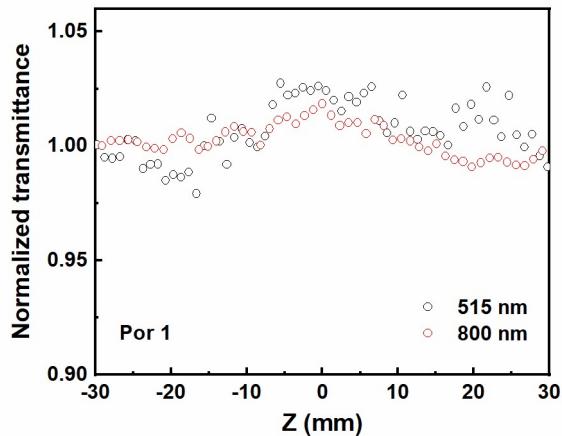


Figure S12. Open-aperture Z-scan curves of Por 1 solutions at 800 nm with 56 nJ pulse energy and at 515 nm with 60 nJ pulse energy.

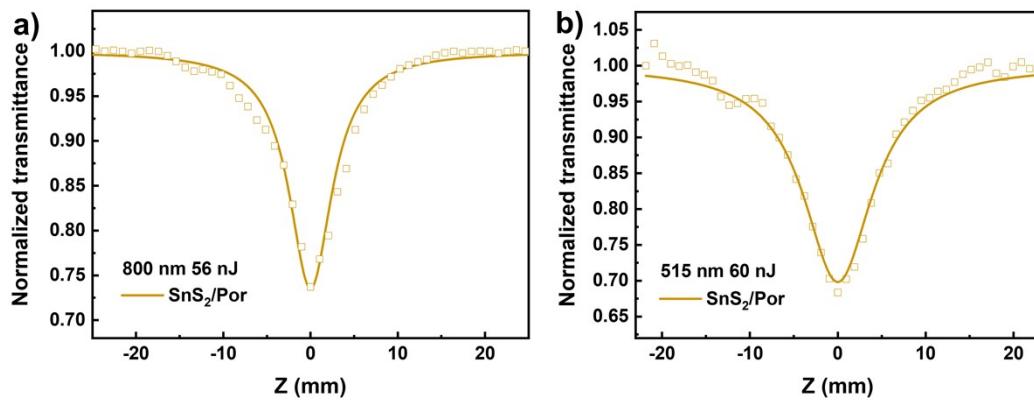


Figure S13. Z-scan curves of the SnS₂/Por blend at 800 nm (a) and 515 nm (b).

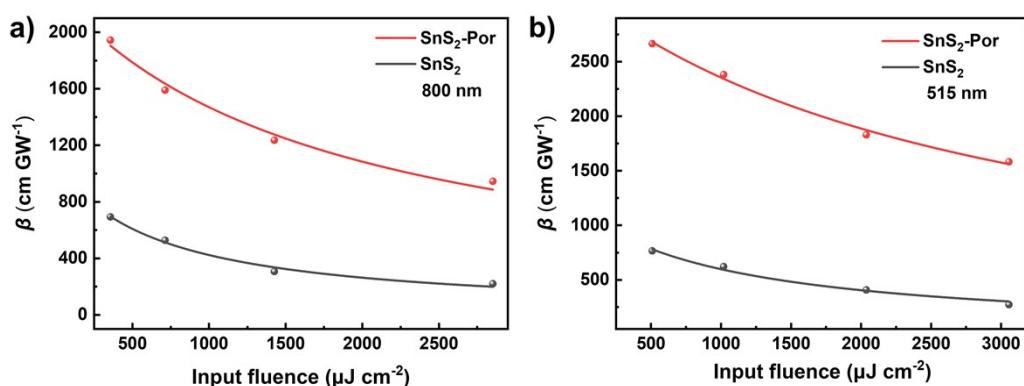


Figure S14. TPA saturation fitting at 800 nm (a) and 515 nm (b).

Table S1. Atom percentages of the SnS₂ nanosheets and the SnS₂-Por nanohybrid.

Element	Atom (%)	
	SnS ₂	SnS ₂ -Por
Sn 3d	14.21	11.70
S 2p	25.55	20.76
C 1s	37.81	43.53
O 1s	22.44	16.47
N 1s	-	7.54

Table S2. Optical limiting thresholds (F_{th}) at selected wavelengths.

Materials	Laser	$F_{\text{th}} (\text{mJ cm}^{-2})$
SnS ₂ -Por (this work)	515 nm 35 fs 1 kHz	1.65
Azine derivative ¹	515 nm 190 fs 20 Hz	16
hydrazone derivative ²	515 nm 190 fs 20 Hz	2.75
SWNTs ³	532 nm 5 ns	250
SWNT-TPP ³	532 nm 5 ns	70
Graphene ⁴	532 nm 6 ns 10 Hz	800
Graphene-Zn-porphyrin ⁴	532 nm 6 ns 10 Hz	200
ZnTPyP-1/PDMS ⁵	532 nm 5 ns 5 Hz	320
WS ₂ ⁶	532 nm 7 ns 10 Hz	880
GO:PVA ⁷	400 nm 100 fs 1 kHz	1.6
SnS ₂ -Por (this work)	800 nm 35 fs 1 kHz	2.74
MoS ₂ /PMMA ⁸	800 nm 100 fs 1 Hz	35.2
WSe ₂ ⁹	800 nm 130 fs 1 kHz	21.6
Pc-pyrene PMMA film ¹⁰	800 nm 90 fs 1 kHz	1.8
Carbon nanodots ¹¹	800 nm 100 fs 1 kHz	74
GO films ¹²	800 nm 100 fs 1 kHz	37
Al-doped InSe thin film ¹³	800 nm 190 fs 10 Hz	14
Li _{0.952} Sn ^{II} _{0.398} Sn ^{IV} _{0.563} S ₂ ¹⁴	800 nm 35 fs 1 kHz	0.8

Table S3. Linear optical and NLO parameters of the SnS₂/Por blend.

Samples	Laser	$\alpha_0 (\text{cm}^{-1})$	T (%)	$\beta_{\text{eff}} (\text{cm GW}^{-1})$
SnS ₂ /Por	800 nm 56 nJ	18833	70	323 ± 10
	515 nm 60 nJ	30828	55	409 ± 10

Table S4. NLO parameters of the SnS₂ nanosheets and the SnS₂-Por nanohybrid

Laser	Samples	$\beta_0 (\text{cm GW}^{-1})$	$I_s (\mu\text{J cm}^{-2})$
800 nm 35 fs	SnS ₂	1083 ± 111	641 ± 135
	SnS ₂ -Por	2280 ± 117	1815 ± 287
515 nm 35 fs	SnS ₂	1140 ± 103	1101 ± 215
	SnS ₂ -Por	3129 ± 76	3041 ± 246

Reference

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